# N-Channel 80 V (D-S) 175 °C MOSFET

DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

• N-Channel Vertical DMOS

• Macro Model (Subcircuit Model)

• Level 3 MOS

• Apply for both Linear and Switching Application

• Accurate over the - 55 °C to + 125 °C Temperature Range

• Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC
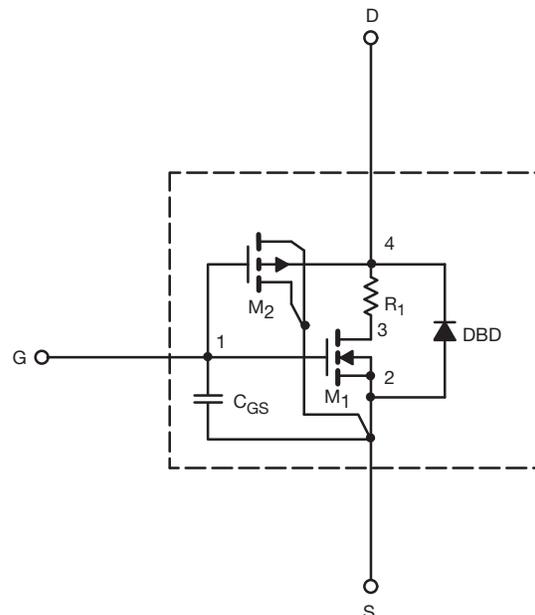
Note
• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	3.4	-	V
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	304	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 40 A	0.013	0.013	Ω
		V_{GS} = 10 V, I_D = 40 A, T_J = 125 °C	0.022	-	
		V_{GS} = 10 V, I_D = 40 A, T_J = 175 °C	0.026	-	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 40 A	49	45	S
Diode Forward Voltage	V_{SD}	I_S = 40 A, V_{GS} = 0 V	0.91	1	V
Dynamic[b]					
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	2091	1960	pF
Output Capacitance	C_{oss}		438	370	
Reverse Transfer Capacitance	C_{rss}		248	200	
Total Gate Charge	Q_g	V_{DS} = 40 V, V_{GS} = 10 V, I_D = 40 A	39	42	nC
Gate-Source Charge	Q_{gs}		7	7	
Gate-Drain Charge	Q_{gd}		13	13	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 1 Ω I_D = 40 A, V_{GEN} = 10 V, R_g = 2.5 Ω	19	12	ns
Rise Time	t_r		29	52	
Turn-Off Delay Time	$t_{d(off)}$		31	25	
Fall Time	t_f		40	10	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 40 A, dI/dt = 100 A/µs	38	45	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)
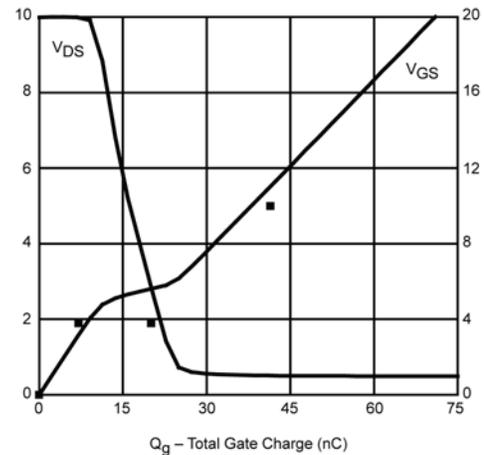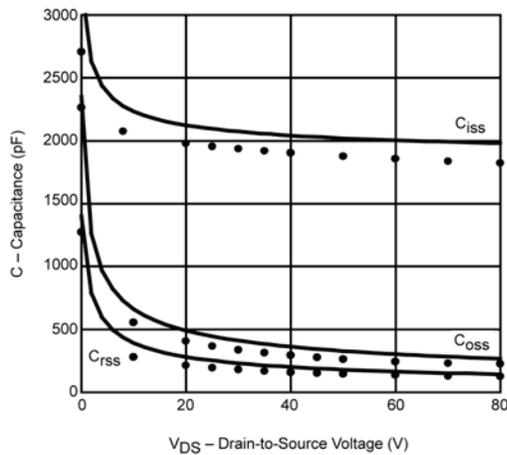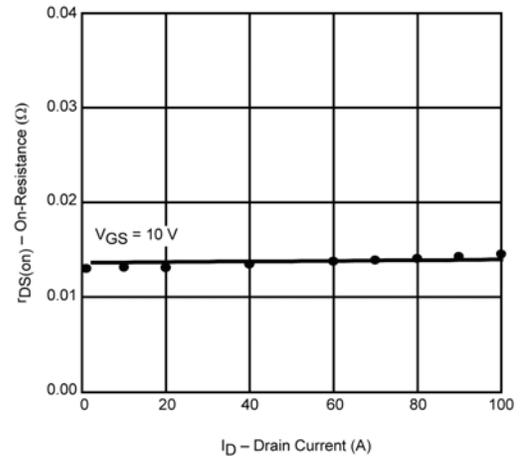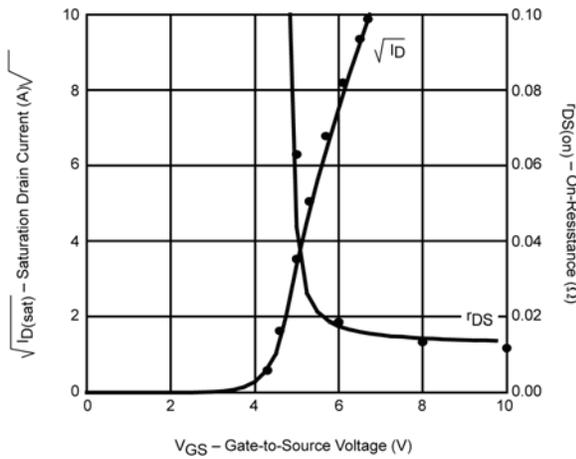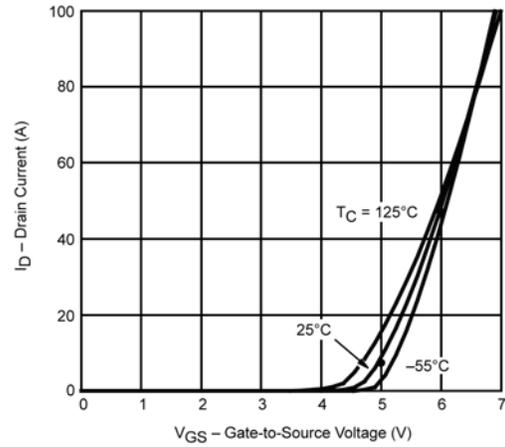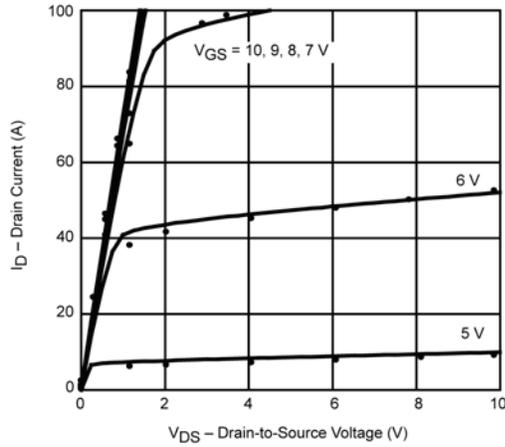
Note
• Dots and squares represent measured data.